

ABSTRACT OF THE DISCLOSURE

A semiconductor device disclosed herein comprises a semiconductor layer which includes a first semiconductor region of a first conductivity type, a base region of a second conductivity type, and a plurality of second semiconductor regions of the first conductivity type; a gate wiring which is formed on the semiconductor layer via a first insulating film; a plurality of main electrodes which are electrically connected to the plurality of second semiconductor regions and which are insulated from the gate wiring, wherein the gate wiring is arranged between the main electrodes and upper surfaces of the main electrodes are higher than an upper surface of the uppermost layer of the gate wiring; and a connecting plate which is directly connected onto uppermost layers of the main electrodes.